



Optoelectronic Devices & Epitaxy Lab (ODEL)

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Institute of Electronics Engineering

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Atomic-Layer-Deposited TCO & CPO for Optoelectronic Devices

TCO: Transparent Conductive Oxide CPO: Conformal Passivating Oxide

GZO, AZO, Al_2O_3
(IZO)
(SiO_2)
(AlN)
(HfO_2)
...



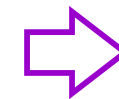
III-N Green / Blue / UV LEDs (High-Speed / mLEDA)
III-V Red / NIR LEDs (High-Speed / Broadband)
III-N PIN Diodes (Power / UV-Sensor)
III-V PIN Photodiodes (High-Speed / Broadband)
Si-Based MOEMS Tunable Optical Filter
III-N MOSFET

SWIR Optoelectronic Devices & Applications

SWIR: Short-Wave Infrared (900 - 2500 nm Wavelength Band)

Broadband Light Source
Tunable Optical Filter
SWIR Photodiode

Micro Tungsten Lamp
NIR Broadband LED
Mini Filter Wheel
Si-Based MOEMS Filter
Broadband
Diode Array



Mini Spectrometer
Micro Spectrometer
Portable Biosensor

吳孟奇

著作目錄

期刊論文

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